Product data sheet

1. General description

Planar passivated high commutation three quadrant triac in a SOT78 (TO-220AB) plastic package. This "series F" triac balances the requirements of commutation performance and gate sensitivity and is intended for interfacing with low power drivers and logic ICs including microcontrollers in higher noise environments.

2. Features and benefits

- 3Q technology for improved noise immunity
- Direct triggering from low power drivers and logic ICs
- · High commutation capability
- High voltage capability
- · Intermediate sensitivity for maximum noise immunity and logic level triggering
- Planar passivated for voltage ruggedness and reliability
- Triggering in three quadrants only

3. Applications

- · Electronic thermostats
- · General purpose motor controls

4. Quick reference data

Table 1. Quick reference data

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|---------------------|------------------------------------------|------------------------------------------------------------------------------------------------------------------------------------------|-----|-----|-----|------|
| V_{DRM} | repetitive peak off- state voltage | | - | - | 600 | V |
| I _{T(RMS)} | RMS on-state current | full sine wave; $T_{mb} \le 102 ^{\circ}\text{C}$; $\overline{\text{Fig. 1}}$; $\overline{\text{Fig. 2}}$; $\overline{\text{Fig. 3}}$ | - | - | 8 | А |
| I _{TSM} | non-repetitive peak on- state current | full sine wave; $T_{j(init)}$ = 25 °C; t_p = 20 ms; Fig. 4; Fig. 5 | - | - | 65 | А |
| | | full sine wave; $T_{j(init)}$ = 25 °C; t_p = 16.7 ms | - | - | 72 | А |
| Tj | junction temperature | | - | - | 125 | °C |
| Static charac | cteristics | | | | | |
| I _{GT} | gate trigger current | $V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2+ \text{ G+;}$ $T_j = 25 \text{ °C; } \underline{\text{Fig. 7}}$ | - | - | 25 | mA |
| | | $V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2 + G-;$ $T_j = 25 \text{ °C; } Fig. 7$ | - | - | 25 | mA |

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| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|-----------------------|---------------------------------------|--------------------------------------------------------------------------------------------------------------|-----|-----|------|------|
| | | $V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; \text{ T2- G-};$ $T_j = 25 \text{ °C}; \frac{\text{Fig. 7}}{}$ | - | - | 25 | mA |
| I _H | holding current | V _D = 12 V; T _j = 25 °C; <u>Fig. 9</u> | _ | - | 30 | mA |
| V_{T} | on-state voltage | I _T = 10 A; T _j = 25 °C; <u>Fig. 10</u> | - | - | 1.65 | V |
| Dynamic char | acteristics | | | | | |
| dV _D /dt | rate of rise of off-state voltage | V_{DM} = 402 V; T_j = 110 °C; (V_{DM} = 67% of V_{DRM}); exponential waveform; gate open circuit | 70 | - | - | V/µs |
| dl _{com} /dt | rate of change of commutating current | V_D = 400 V; T_j = 125 °C; $I_{T(RMS)}$ = 8 A; dV_{com}/dt = 0.1 V/µs; gate open circuit | 20 | - | - | A/ms |
| | | V_D = 400 V; T_j = 125 °C; $I_{T(RMS)}$ = 8 A; dV_{com}/dt = 10 V/ μ s; gate open circuit; Fig. 12 | 14 | - | - | A/ms |

5. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description | Simplified outline | Graphic symbol |
|-----|--------|--------------------------------|--------------------|----------------|
| 1 | T1 | main terminal 1 | mb | T2—71 |
| 2 | T2 | main terminal 2 | ├ | G sym051 |
| 3 | G | gate | | Symosi |
| mb | T2 | mounting base; main terminal 2 | | |
| | | | TO-220AB (SOT78) | |

6. Ordering information

Table 3. Ordering information

| Type number | Package | Package | | | | |
|-------------|----------|----------------------------------------------------------------------------------|---------|--|--|--|
| | Name | Description | Version | | | |
| BTA208-600F | TO-220AB | plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB | SOT78 | | | |

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7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol | Parameter | Conditions | Min | Max | Unit |
|---------------------|------------------------------------------|----------------------------------------------------------------------------|-----|-----|------|
| V_{DRM} | repetitive peak off-state voltage | | - | 600 | V |
| I _{T(RMS)} | RMS on-state current | full sine wave; $T_{mb} \le 102 ^{\circ}\text{C}$; Fig. 1; Fig. 2; Fig. 3 | - | 8 | Α |
| I _{TSM} | non-repetitive peak on- state current | full sine wave; $T_{j(init)}$ = 25 °C; t_p = 20 ms; Fig. 4; Fig. 5 | - | 65 | Α |
| | | full sine wave; T _{j(init)} = 25 °C; t _p = 16.7 ms | - | 72 | Α |
| l ² t | I ² t for fusing | t _p = 10 ms; SIN | - | 21 | A²s |
| dl _T /dt | rate of rise of on-state current | I _G = 0.2 A | - | 100 | A/µs |
| I _{GM} | peak gate current | | - | 2 | Α |
| P _{GM} | peak gate power | | - | 5 | W |
| $P_{G(AV)}$ | average gate power | over any 20 ms period | - | 0.5 | W |
| T _{stg} | storage temperature | | -40 | 150 | °C |
| T _j | junction temperature | | - | 125 | °C |

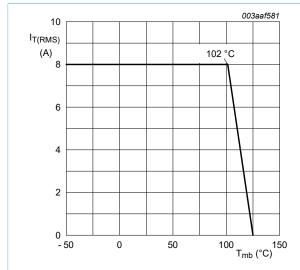


Fig. 1. RMS on-state current as a function of mounting base temperature; maximum values

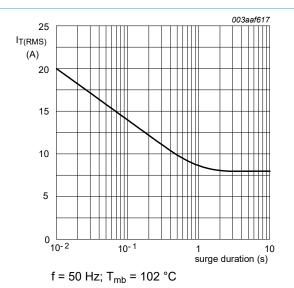


Fig. 2. RMS on-state current as a function of surge duration; maximum values

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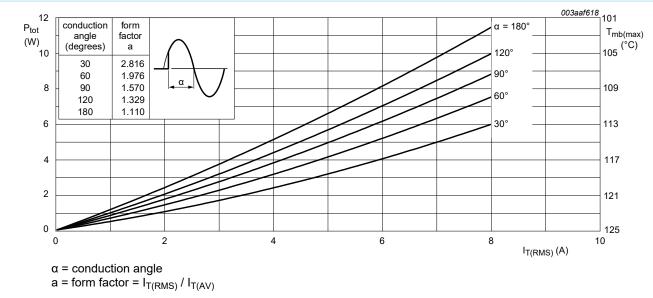


Fig. 3. Total power dissipation as a function of RMS on-state current; maximum values

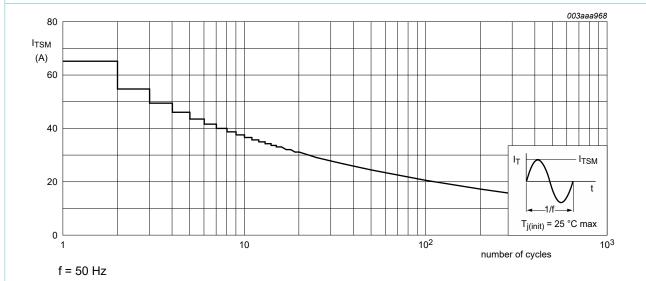
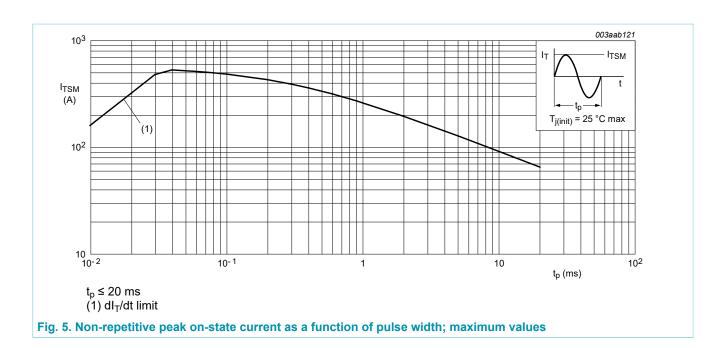


Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values

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8. Thermal characteristics

Table 5. Thermal characteristics

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|-----------------------|------------------------------------------------------------|--------------------|-----|-----|-----|------|
| R _{th(j-mb)} | thermal resistance | full cycle; Fig. 6 | - | - | 2 | K/W |
| | rom junction to nounting base | half cycle; Fig. 6 | - | - | 2.4 | K/W |
| $R_{th(j-a)}$ | thermal resistance from junction to ambient free air | in free air | - | 60 | - | K/W |

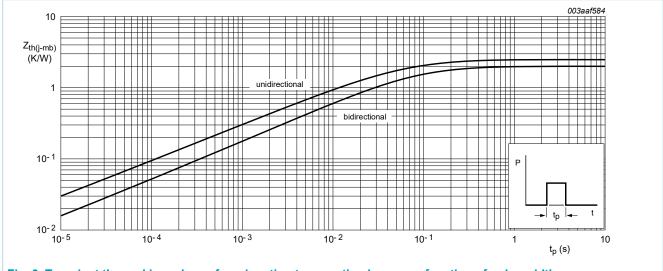


Fig. 6. Transient thermal impedance from junction to mounting base as a function of pulse width

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9. Characteristics

Table 6. Characteristics

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|-----------------------|---------------------------------------|--------------------------------------------------------------------------------------------------------------|------|-----|------|------|
| Static char | acteristics | | ' | | | |
| I _{GT} | gate trigger current | $V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ G+;$ $T_j = 25 \text{ °C}; Fig. 7$ | - | - | 25 | mA |
| | | $V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2 + G-;$ $T_j = 25 \text{ °C; } Fig. 7$ | - | - | 25 | mA |
| | | $V_D = 12 \text{ V; } I_T = 0.1 \text{ A; T2- G-;}$ $T_j = 25 \text{ °C; } Fig. 7$ | - | - | 25 | mA |
| L | latching current | $V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2+ G+;$ $T_j = 25 \text{ °C}; Fig. 8$ | - | - | 30 | mA |
| | | $V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2+ G-;$ $T_j = 25 \text{ °C}; Fig. 8$ | - | - | 30 | mA |
| | | $V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; \text{ T2- G-};$ $T_j = 25 ^{\circ}\text{C}; \text{ Fig. 8}$ | - | - | 40 | mA |
| l _H | holding current | V _D = 12 V; T _j = 25 °C; <u>Fig. 9</u> | - | - | 30 | mA |
| V _T | on-state voltage | I _T = 10 A; T _j = 25 °C; <u>Fig. 10</u> | - | - | 1.65 | V |
| V_{GT} | gate trigger voltage | $V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T_j = 25 \text{ °C};$ Fig. 11 | - | 0.7 | 1 | V |
| | | V _D = 400 V; I _T = 0.1 A; T _j = 125 °C; Fig. 11 | 0.25 | 0.4 | - | V |
| I _D | off-state current | V _D = 600 V; T _j = 125 °C | - | 0.1 | 0.5 | mA |
| Dynamic cl | haracteristics | | | | | |
| dV _D /dt | rate of rise of off-state voltage | V_{DM} = 402 V; T_j = 110 °C; (V_{DM} = 67% of V_{DRM}); exponential waveform; gate open circuit | 70 | - | - | V/µs |
| dl _{com} /dt | rate of change of commutating current | V_D = 400 V; T_j = 125 °C; $I_{T(RMS)}$ = 8 A; dV_{com}/dt = 0.1 V/ μ s; gate open circuit | 20 | - | - | A/ms |
| | | V_D = 400 V; T_j = 125 °C; $I_{T(RMS)}$ = 8 A; dV_{com}/dt = 10 V/ μ s; gate open circuit; Fig. 12 | 14 | - | - | A/ms |

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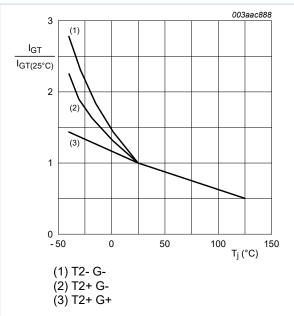


Fig. 7. Normalized gate trigger current as a function of junction temperature

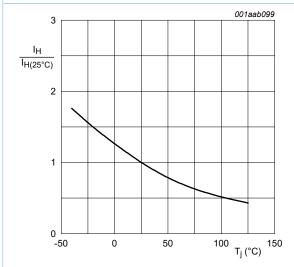


Fig. 9. Normalized holding current as a function of junction temperature

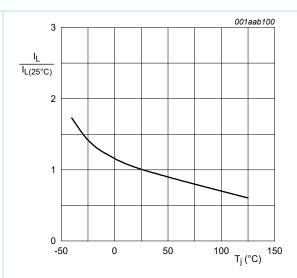
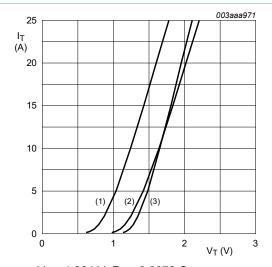


Fig. 8. Normalized latching current as a function of junction temperature



 V_o = 1.264 V; R_s = 0.0378 Ω

(1) $T_j = 125$ °C; typical values (2) $T_j = 125$ °C; maximum values (3) $T_j = 25$ °C; maximum values

Fig. 10. On-state current as a function of on-state voltage

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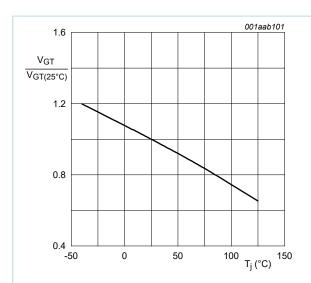


Fig. 11. Normalized gate trigger voltage as a function of junction temperature

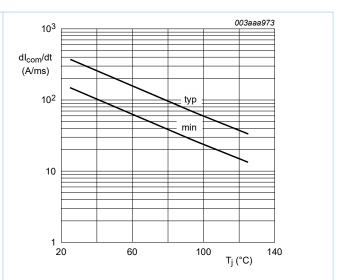
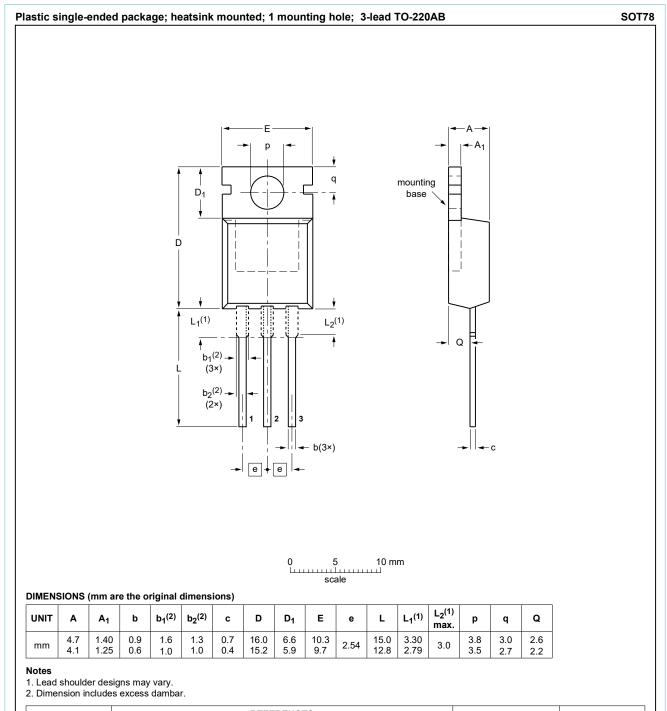


Fig. 12. Rate of change of commutating current as a function of junction temperature; typical and minimum values

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10. Package outline



| | EUROPEAN | ISSUE DATE |
|-----------------------------|------------|---------------------------------|
| VERSION IEC JEDEC JEITA | PROJECTION | ISSUE DATE |
| SOT78 3-lead TO-220AB SC-46 | | 08-04-23 08-06-13 |

Fig. 13. Package outline TO-220AB (SOT78)

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Data sheet status

| Document status [1][2] | Product status [3] | Definition |
|--------------------------------------|--------------------|---------------------------------------------------------------------------------------|
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Date of release: 19 September 2018

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